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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
09/925,952	08/10/2001	Tetsuo Endoh	900-397	5574
23117 7	7590 09/13/2004		EXAMINER	
NIXON & VANDERHYE, PC			NGUYEN, JOSEPH H	
1100 N GLEBE ROAD 8TH FLOOR		ART UNIT	PAPER NUMBER	
	, VA 22201-4714		2815	
			DATE MAILED: 09/13/200	4

Please find below and/or attached an Office communication concerning this application or proceeding.

		Me	<i>_</i> .
*	Application No.	Applicant(s)	
Office Action Summan	09/925,952	ENDOH ET AL.	
Office Action Summary	Examiner	Art Unit	
	Joseph Nguyen	2815	
The MAILING DATE of this communication Period for Reply	appears on the cover sheet w	th the correspondence address	
A SHORTENED STATUTORY PERIOD FOR RE THE MAILING DATE OF THIS COMMUNICATIO - Extensions of time may be available under the provisions of 37 CFR after SIX (6) MONTHS from the mailing date of this communication. - If the period for reply specified above is less than thirty (30) days, a - If NO period for reply is specified above, the maximum statutory per - Failure to reply within the set or extended period for reply will, by sta Any reply received by the Office tater than three months after the magnitude of the patent term adjustment. See 37 CFR 1.704(b).	N. R 1.136(a). In no event, however, may a reply within the statutory minimum of this id will apply and will expire SIX (6) MOI atute, cause the application to become Al	eply be timely filed by (30) days will be considered timely. ITHS from the mailing date of this communication. BANDONED (35 U.S.C. § 133).	
Status			
1) Responsive to communication(s) filed on 13	3 August 2004.		
2a)⊠ This action is FINAL . 2b)☐ T	his action is non-final.		
3) Since this application is in condition for allocation closed in accordance with the practice under the condition of the	•	• •	
Disposition of Claims			
4) ☐ Claim(s) 1,3,5,7-9,11-17,19,29,31-46 and 4 4a) Of the above claim(s) is/are witho 5) ☐ Claim(s) 19,37-39 and 55 is/are allowed. 6) ☐ Claim(s) 1,3,5,7-9,11-17,29,31-36,39-46,49 7) ☐ Claim(s) is/are objected to. 8) ☐ Claim(s) are subject to restriction and	drawn from consideration. 9-54 and 56 is/are rejected.	plication.	
Application Papers			
9) ☐ The specification is objected to by the Exam 10) ☑ The drawing(s) filed on 10 August 2001 is/a Applicant may not request that any objection to a Replacement drawing sheet(s) including the cor 11) ☐ The oath or declaration is objected to by the	re: a)⊠ accepted or b)⊡ ol the drawing(s) be held in abeya rection is required if the drawing	nce. See 37 CFR 1.85(a). (s) is objected to. See 37 CFR 1.121(d).	
Priority under 35 U.S.C. § 119			
12) Acknowledgment is made of a claim for fore a) All b) Some * c) None of: 1. Certified copies of the priority docum 2. Certified copies of the priority docum 3. Copies of the certified copies of the papplication from the International Bur * See the attached detailed Office action for a	ents have been received. ents have been received in A priority documents have beer reau (PCT Rule 17.2(a)).	opplication No received in this National Stage	
Attachment(s) 1) Notice of References Cited (PTO-892)	4) ☐ Interview	Summary (PTO-413)	
 Notice of References Cited (PTO-052) Notice of Draftsperson's Patent Drawing Review (PTO-948) Information Disclosure Statement(s) (PTO-1449 or PTO/SB. Paper No(s)/Mail Date 	Paper No	s)/Mail Date nformal Patent Application (PTO-152)	

DETAILED ACTION

Claim Rejections - 35 USC § 102

The following is a quotation of the appropriate paragraphs of 35 U.S.C. 102 that form the basis for the rejections under this section made in this Office action:

A person shall be entitled to a patent unless -

(b) the invention was patented or described in a printed publication in this or a foreign country or in public use or on sale in this country, more than one year prior to the date of application for patent in the United States.

Claims 1, 3, 5, 7-9, 11-17, 29, 31-36, 39-46, 49-54, 56 are rejected under 35 U.S.C. 102(b) as being anticipated by Burns Jr, et al.

Regarding claim 1, Burns, Jr. et al discloses on figure 10 a semiconductor memory comprising a first conductivity type semiconductor substrate 235; and one or more memory cells comprising an island like semiconductor layer 230, a charge storage layer 265 and a control gate 275, the charge storage layer and the control gate being formed to entirely or partially encircle a sidewall of the island like semiconductor layer, wherein an active region of at least one of said memory cells is electrically insulated from the semiconductor substrate by a second conductivity type impurity diffusion layer 215 formed in the semiconductor substrate or in the island like semiconductor layer and means for forming a depletion layer formed at a junction between the second conductivity type impurity diffusion layer 215 and the semiconductor substrate 235 or the island like semiconductor layer 230.

Regarding claims 5, 7-9, 11-17, 29, 31-36, 39-46, 49-54, 56, Burns Jr, et al. discloses on figure 10 all the structures set forth in the claimed invention.

Allowable Subject Matter

Claims 19, 37-38, 55 are allowed.

Response to Arguments

Applicant's arguments filed on 08/13/2004 have been fully considered but they are not persuasive.

With respect to claims 1, 5, 36, 46, applicant argues that Burns does not disclose or suggest "means for forming a depletion layer formed at a junction between the second conductivity type impurity diffusion layer and the semiconductor substrate" as now recited in amended claims 1, 5, 36 and 46. However, it is well known in the art that the depletion layer is inherently formed at the PN junction by applying different potentials to the diffusion layer and the substrate. In figure 10 of Burns, the second conductivity type impurity diffusion layer 215 and the semiconductor substrate 235 are the means that create a PN junction in which a depletion layer is formed. Therefore, Burns discloses means for forming a depletion layer formed at a junction between the second conductivity type impurity diffusion layer and the semiconductor substrate.

Applicant's amendment necessitated the new ground(s) of rejection presented in this Office action. Accordingly, **THIS ACTION IS MADE FINAL**. See MPEP § 706.07(a). Applicant is reminded of the extension of time policy as set forth in 37. CFR 1.136(a).

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Art Unit: 2815

A shortened statutory period for reply to this final action is set to expire THREE MONTHS from the mailing date of this action. In the event a first reply is filed within TWO MONTHS of the mailing date of this final action and the advisory action is not mailed until after the end of the THREE-MONTH shortened statutory period, then the shortened statutory period will expire on the date the advisory action is mailed, and any extension fee pursuant to 37 CFR 1.136(a) will be calculated from the mailing date of the advisory action. In no event, however, will the statutory period for reply expire later than SIX MONTHS from the date of this final action.

Conclusion

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Joseph Nguyen whose telephone number is (571) 272-1734. The examiner can normally be reached on Monday-Friday, 7:30 am- 4:30 pm

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Tom Thomas can be reached on (571) 272-1664. The fax phone number for the organization where this application or proceeding is assigned is (703) 872-9306 for regular communications.

JN September 9, 2004

> JEROME JACKSON PRIMARY EXAMINER